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**(54) METHOD OF  
MEASURING PATTERN  
OVERLAY ACCURACY**

(57) Abstract:

**PURPOSE:** To prevent an error by forming a first alignment mark in first step, then covering the top with a film which transmits an irradiated beam used at the time of alignment, and flattening the top of the film.

**CONSTITUTION:** An alignment mark 2a formed in a recess shape in first step on a semiconductor substrate 1 is covered with a thin film 6 of a material which transmits an alignment light, and the film is so selected that the upper face becomes flat in response to a mark step. Then, an alignment mark 5 is formed on a resist film 5 formed in second step. The marks 2a, 5 are scanned by a laser light, scattered light from the step of the mark is detected to accurately measure the overlay deviation.

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